



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	7.5mΩ @ V _{GS} = 10V	30A
60V	11.5mΩ @ V _{GS} = 4.5V	25A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- · Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

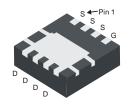
- Low Rds(ON) Ensures On-State Losses Are Minimized
- Excellent Q_{GD} x R_{DS}(ON) Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8, Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable And Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.008 grams (Approximate)

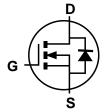
PowerDI3333-8







Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6010LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT6010LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SG6 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	Vgss	±20	V	
$T_{A} = +25$ $T_{A} = +70$		ID	13 11	А
Continuous Drain Current (Note 5) Vos = 10V	$T_C = +25$ °C $T_C = +70$ °C	lo	30 24	А
Maximum Continuous Body Diode Forward Current (Note 5)	ls	3	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Avalanche Current, L=0.1mH		las	20	А
Avalanche Energy, L=0.1mH	Eas	20	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	$T_A = +25$ °C	PD	2.2	W	
Total Power Dissipation (Note 5)	$T_C = +25^{\circ}C$	PD	41		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Р	55		
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	$R_{\theta JA}$	35	°C/W	
Thermal Resistance, Junction to Case (Note 5)	Rejc	3			
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	1	1	1	μA V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	Vgs(th)	0.8		2	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	Pag(au)	-	6	7.5	mΩ	$V_{GS} = 10V, I_{D} = 20A$
Static Drain-Source On-Nesistance	RDS(ON)	_	7.8	11.5		$V_{GS} = 4.5V, I_{D} = 20A$
Diode Forward Voltage	V _{SD}	l	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	2,090			V _{DS} = 30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	-	746	_	pF	
Reverse Transfer Capacitance	Crss	-	38.5			
Gate Resistance	RG	1	0.59	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (Vgs = 4.5V)	QG	-	19.3			
Total Gate Charge (V _{GS} = 10V)	Q_{G}	-	41.3	_	nC	V _{DS} = 30V, I _D = 20A
Gate-Source Charge	Qgs	-	6.0		IIC	VDS = 30V, ID = 20A
Gate-Drain Charge	Q_{GD}	_	8.8	_		
Turn-On Delay Time	td(on)	_	5.7	_		
Turn-On Rise Time	t _R	_	4.3	_	ns	V _{DD} = 30V, V _{GS} = 10V,
Turn-Off Delay Time	tD(OFF)	_	23.4	_	115	$I_D = 20A$, $R_G = 3\Omega$
Turn-Off Fall Time	tF	_	9.7	_		

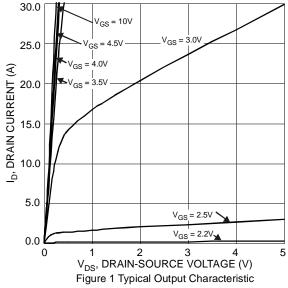
Notes:

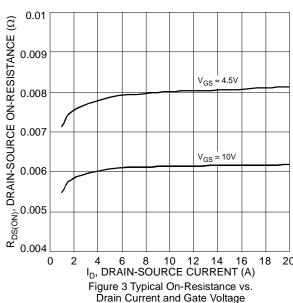
^{5.} ReJA is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. ReJC is guaranteed by design while ReJA is determined by the user's board design.

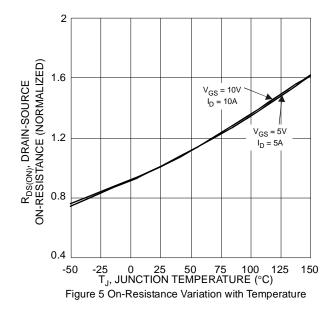
^{6.} Short duration pulse test used to minimize self-heating effect.

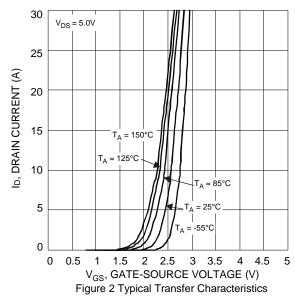
^{7.} Guaranteed by design. Not subject to product testing.

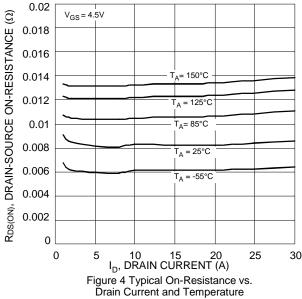


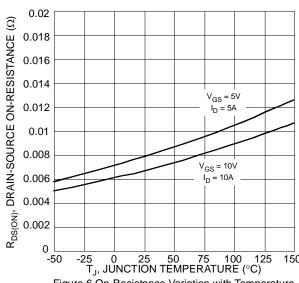














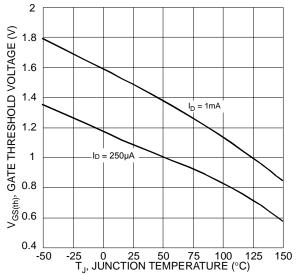
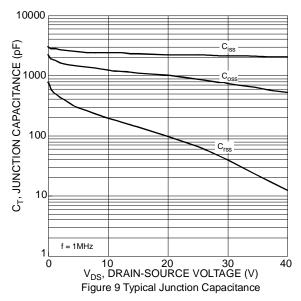
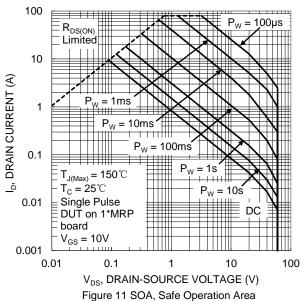
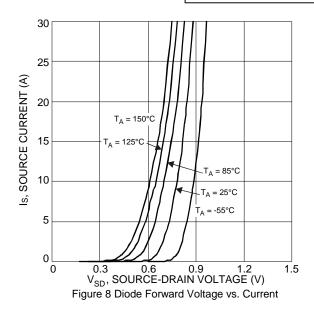
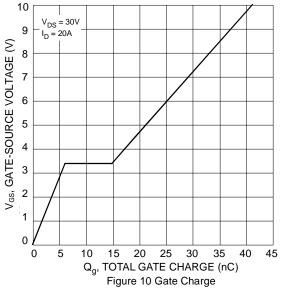


Figure 7 Gate Threshold Variation vs. Junction Temperature











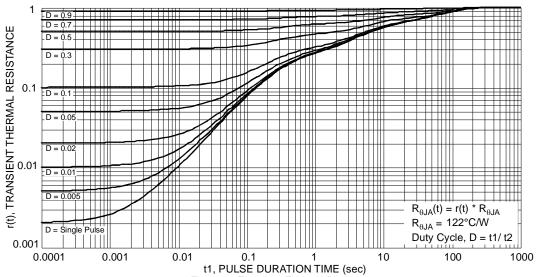


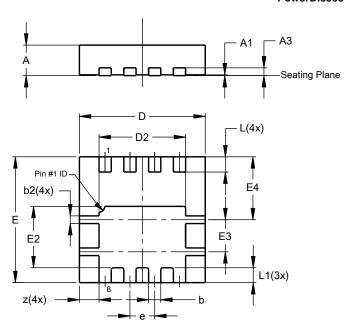
Figure 12 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

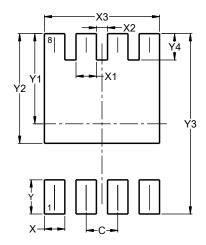


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
А3	_	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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